

General Description

The MAX4838-MAX4841 are overvoltage protection ICs that protect low-voltage systems against voltages of up to 28V. If the input voltage exceeds the overvoltage trip level, the MAX4838-MAX4841 turn off the low-cost external N-channel FET(s) to prevent damage to the protected components. An internal charge pump eliminates the need for external capacitors and drives the FET gate for a simple, robust solution.

The MAX4838/MAX4839 have a 7.4V overvoltage threshold, and the MAX4840/MAX4841 have a 5.8V overvoltage threshold. All devices have an undervoltage lockout threshold of 3.25V. In addition to the single FET configuration, the devices can be configured with back-to-back external FETs to prevent currents from being back-driven into the adapter.

On power-up, the device waits for 50ms before driving GATE high. FLAG is held low for an additional 50ms after GATE goes high before deasserting. The MAX4838/MAX4840 have an open-drain FLAG output, and the MAX4839/MAX4841 have a push-pull FLAG output. The FLAG output asserts immediately to an overvoltage fault.

Additional features include a 15kV ESD-protected input (when bypassed with a 1µF capacitor) and a shutdown pin (EN) to turn off the device (MAX4838/MAX4840).

All devices are offered in a small 6-pin SC70 package and are specified for operation from -40°C to +85°C.

Applications

Cell Phones Digital Still Cameras PDAs and Palmtop Devices MP3 Players

Selector Guide

PART	UVLO THRESHOLD (V)	OV TRIP LEVEL (V)	EN INPUT	FLAG OUTPUT
MAX4838EXT-T	3.25	7.4	Yes	Open-Drain
MAX4839EXT-T	3.25	7.4	No	Push-Pull
MAX4840EXT-T	3.25	5.8	Yes	Open-Drain
MAX4841EXT-T	3.25	5.8	No	Push-Pull

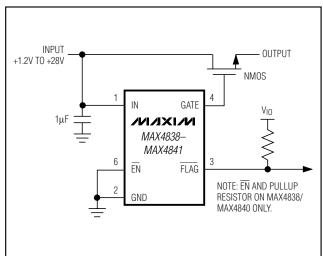
Features

- ♦ Overvoltage Protection Up to 28V
- ♦ Preset 7.4V or 5.8V Overvoltage Trip Level
- ♦ Drive Low-Cost NMOS FET
- ♦ Internal 50ms Startup Delay
- ♦ Internal Charge Pump
- **♦ Undervoltage Lockout**
- ♦ 15kV ESD-Protected Input
- ♦ Voltage Fault FLAG Indicator
- ♦ 6-Pin SC70 Package

Ordering Information

PART	PART TEMP RANGE		TOP MARK
MAX4838EXT-T	-40°C to +85°C	6 SC70-6	ABW
MAX4839EXT-T	-40°C to +85°C	6 SC70-6	ABY
MAX4840EXT-T	-40°C to +85°C	6 SC70-6	ABX
MAX4841EXT-T	-40°C to +85°C	6 SC70-6	ABZ

Typical Operating Circuit



Pin Configuration appears at end of data sheet.

MIXIM

Maxim Integrated Products 1

For pricing, delivery, and ordering information, please contact Maxim/Dallas Direct! at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

ABSOLUTE MAXIMUM RATINGS

IN to GND0.3V to +30V	Operating Temperature Range40°C to +85°C
GATE to GND0.3V to +12V	Junction Temperature+150°C
EN, FLAG to GND0.3V to +6V	Storage Temperature Range65°C to +150°C
Continuous Power Dissipation (T _A = +70°C)	Lead Temperature (soldering, 10s)+300°C
6-Pin SC70 (derate 3.1mW/ $^{\circ}$ C above +70 $^{\circ}$ C) 245mW	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{IN} = +5V, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.}$ Typical values are at $T_A = +25^{\circ}C.)$ (Note 1)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Input Voltage Range	V _{IN}		1.2		28.0	V	
Undervoltage Lockout Threshold	UVLO	V _{IN} falling	3.0	3.25	3.5	V	
Undervoltage Lockout Hysteresis					50		mV
Overveltage Trip Level	OVLO	MAX4838/MAX4839	7.0	7.4	7.8	V	
Overvoltage Trip Level	OVLO	MAX4840/MAX4841	5.5	5.8	6.1		
Overvoltage Trip Level Hyeteresis		MAX4838/MAX4839			100		mV
Overvoltage Trip Level Hysteresis		MAX4840/MAX4841		80			
IN Supply Current	I _{IN}	No load, $\overline{EN} = GND$	or 5.5V, V _{IN} = 5.4V		140	240	μΑ
UVLO Supply Current		V _{IN} = 2.9V				150	μΑ
GATE Voltage	VGATE	IGATE sourcing 1µA		9		10	V
GATE Pulldown Current	I _{PD}	V _{IN} > V _{OVLO} , V _{GATE} = 5.5V			60		mA
FLAC Output Law Valtage	V/	1.2V ≤ V _{IN} < UVLO, I _{SINK} = 50µA				0.4	V
FLAG Output Low Voltage	V _{OL}	V _{IN} ≥ OVLO, I _{SINK} = 1mA				0.4	V
FLAG Output High Voltage	VoH	ISOURCE = 100μA, FLAG deasserted, MAX4839/MAX4841		2.4			V
FLAG Output High Leakage	Іон	VFLAG = 5.5V, FLAG deasserted, MAX4838/MAX4840				1	μΑ
EN Input High Voltage	V _{IH}	MAX4838/MAX4840		1.47			V
EN Input Low Voltage	VIL	MAX4838/MAX4840				0.65	V
EN Input Leakage	ILKG	MAX4838/MAX4840, <u>EN</u> = GND or 5.5V				1	μΑ
IN ECD voting			Human Body Model		15		147
IN ESD rating		C _{IN} ≥ 1μF	IEC 1000-4-2		15		kV

ELECTRICAL CHARACTERISTICS (continued)

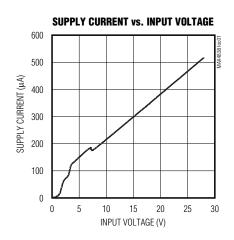
 $(V_{IN} = +5V, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.}$ Typical values are at $T_A = +25^{\circ}C.)$ (Note 1)

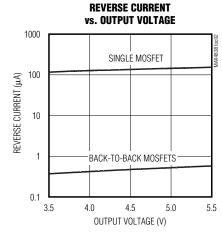
PARAMETER	SYMBOL	L CONDITIONS		TYP	MAX	UNITS
TIMING	•					
Startup Delay	tstart	V _{IN} > V _{UVLO} , V _{GATE} > 0.3V, Figure 1	20	50	80	ms
FLAG Blanking Time	t _{BLANK}	$V_{GATE} = 0.3V, V_{\overline{FLAG}} = 2.4V, Figure 1$	20	50	80	ms
GATE Turn-On Time	tgon	V _{GATE} = 0.3V to 8V, C _{GATE} = 1500pF, Figure 1		7.0		ms
GATE Turn-Off Time	tgoff	V _{IN} increasing from 5V to 8V at 3V/µs, V _{GATE} = 0.3V, C _{GATE} = 1500pF, Figure 2		6	20	μs
FLAG Assertion Delay	tFLAG	V _{IN} increasing from 5V to 8V at 3V/μs, V _{FLAG} = 0.4V, Figure 2		5.8		μs
Initial Overvoltage Fault Delay	tovp	V _{IN} increasing from 0 to 8V, I _{GATE} = 80% of I _{PD} , Figure 3		100		ns
Disable Time	tDIS	VEN = 2.4V, VGATE = 0.3V, MAX4838/MAX4840, Figure 4		580		ns

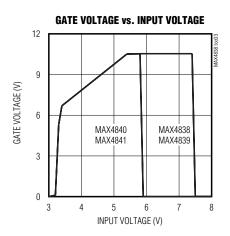
Note 1: All parts are 100% tested at +25°C. Electrical limits across the full temperature range are guaranteed by design and correlation.

_Typical Operating Characteristics

 $(V_{IN} = +5V, MAX4838; Si9936DY external MOSFET in back-to-back configuration; T_A = +25°C, unless otherwise noted.)$

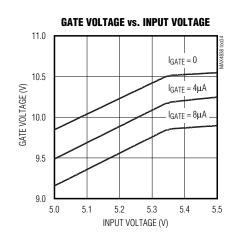


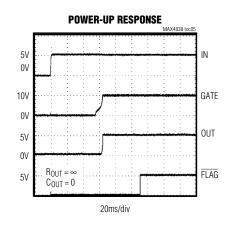


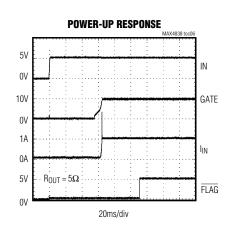


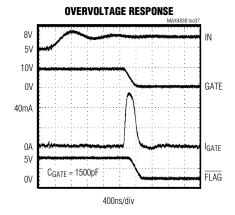
Typical Operating Characteristics (continued)

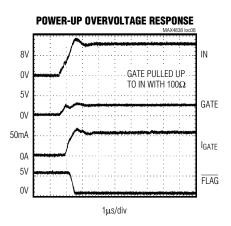
 $(V_{IN} = +5V, MAX4838; Si9936DY external MOSFET in back-to-back configuration; T_A = +25°C, unless otherwise noted.)$

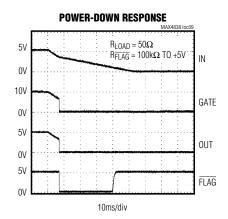












Pin Description

PIN			
MAX4838/ MAX4840	MAX4839/ MAX4841	NAME	FUNCTION
1	1	IN	Input. IN is both the power-supply input and the overvoltage sense input. Bypass IN to GND with a $1\mu F$ capacitor or larger.
2	2	GND	Ground
3	3	FLAG	Fault Indication Output, Active Low. FLAG is asserted low during undervoltage lockout and overvoltage lockout conditions. FLAG is deasserted during normal operation. FLAG is open-drain on the MAX4838/MAX4840, and push-pull on the MAX4839/MAX4841.
4	4	GATE	Gate-Drive Output. GATE is the output of an on-chip charge pump. When $V_{UVLO} < V_{IN} < V_{OVLO}$, GATE is driven high to turn on the external N-channel MOSFET(s).
5	5, 6	N.C.	No Connection. Can be connected to GND.
6		ĒN	Device Enable Input, Active Low. Drive $\overline{\text{EN}}$ low or connect to ground to allow normal device operation. Drive $\overline{\text{EN}}$ high to turn off the external MOSFET.

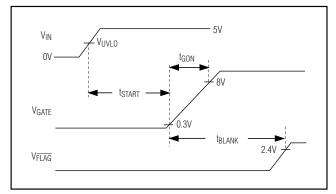


Figure 1. Startup Timing Diagram

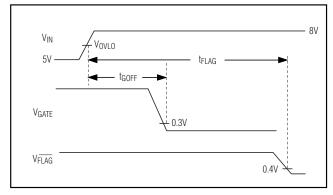


Figure 2. Shutdown Timing Diagram

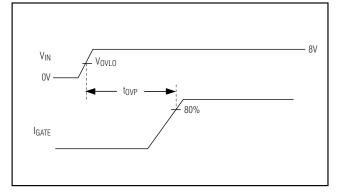


Figure 3. Power-Up Overvoltage Timing Diagram

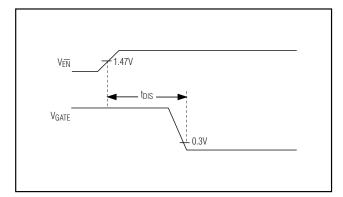


Figure 4. Disable Timing Diagram



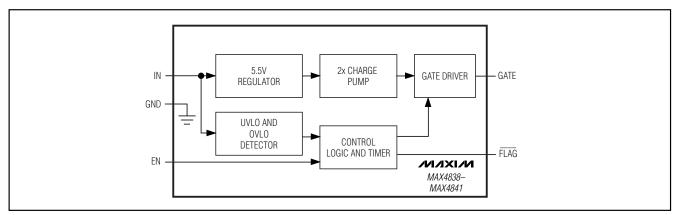


Figure 5. Functional Diagram

Detailed Description

The MAX4838–MAX4841 provide up to 28V overvoltage protection for low-voltage systems. When the input voltage exceeds the overvoltage trip level, the MAX4838–MAX4841 turn off a low-cost external N-channel FET(s) to prevent damage to the protected components. An internal charge pump (Figure 5) drives the FET gate for a simple, robust solution.

Undervoltage Lockout (UVLO)

The MAX4838–MAX4841 have a fixed 3.25V typical undervoltage lockout level (UVLO). When V_{IN} is less than the UVLO, the GATE driver is held low and FLAG is asserted.

Overvoltage Lockout (OVLO)

The MAX4838/MAX4839 have a 7.4V typical overvoltage threshold (OVLO), and the MAX4840/MAX4841 have a 5.8V typical overvoltage threshold. When V_{IN} is greater than OVLO, the GATE driver is held low and FLAG is asserted.

FLAG Output

The FLAG output is used to signal the host system there is a fault with the input voltage. FLAG asserts immediately to an overvoltage fault. FLAG is held low for 50ms after GATE turns on before deasserting.

The MAX4839 and MAX4841 have a push-pull \overline{FLAG} output. The output high voltage is proportional to V_{IN} for V_{IN} up to 5.5V, and fixed at 5.5V when V_{IN} > 5.5V.

The MAX4838 and MAX4840 have an open-drain FLAG output. Connect a pullup resistor from FLAG to the logic I/O voltage of the host system.

EN Enable Input

EN is an active-low enable input on the MAX4838 and MAX4840 only. Drive EN low or connect to ground to

enable normal device operation. Drive $\overline{\text{EN}}$ high to force the external MOSFET(s) off. $\overline{\text{EN}}$ does not override an OVLO or UVLO fault.

GATE Driver

An on-chip charge pump is used to drive GATE above IN, allowing the use of low-cost N-channel MOSFETS. The charge pump operates from the internal 5.5V regulator.

The actual GATE output voltage tracks approximately two times V_{IN} until V_{IN} exceeds 5.5V or the OVLO trip level is exceeded, whichever comes first. The MAX4838/MAX4839 have a 7.4V typical OVLO, therefore GATE remains relatively constant at about 10.5V for 5.5V < V_{IN} < 7.4V. The MAX4840/MAX4841 have a 5.8V typical OVLO, but this can be as low as 5.5V. The MAX4840/MAX4841 in practice may never actually achieve the full 10.5V GATE output. The GATE output voltage as a function of input voltage is shown in the Typical Operating Characteristics.

Device Operation

The MAX4838–MAX4841 have an on-board state machine to control device operation. A flowchart is shown in Figure 6. On initial power-up, if V_{IN} < UVLO or if V_{IN} > OVLO, GATE is held at 0V, and \overline{FLAG} is low.

If UVLO < V_{IN} < OVLO and $\overline{\text{EN}}$ is low, the device enters startup after a 50ms internal delay. The internal charge pump is enabled, and GATE begins to be driven above V_{IN} by the internal charge pump. $\overline{\text{FLAG}}$ is held low during startup until the $\overline{\text{FLAG}}$ blanking period expires, typically 50ms after the GATE starts going high. At this point the device is in its on state.

At any time if V_{IN} drops below UVLO, FLAG is driven low and GATE is driven to ground.

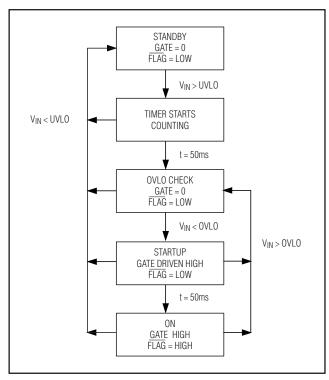


Figure 6. State Diagram

Applications Information MOSFET Configuration

The MAX4838–MAX4841 can be used with either a single MOSFET configuration as shown in the *Typical Operating Circuit*, or can be configured with a back-to-back MOSFET as shown in Figure 7.

The MAX4838–MAX4841 can drive either a single MOSFET or back-to-back MOSFETs. The back-to-back configuration has almost zero reverse current when the input supply is below the output.

If reverse current leakage is not a concern, a single MOSFET can be used. This approach has half the loss of the back-to-back configuration when used with similar MOSFET types, and is a lower cost solution. Note that if the input is actually pulled low, the output is pulled low as well due to the parasitic body diode in the MOSFET. If this is a concern, then the back-to-back configuration should be used.

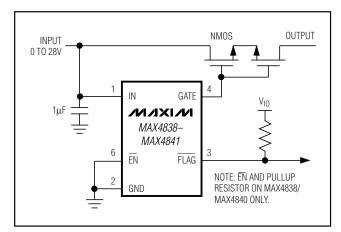


Figure 7. Back-to-Back External MOSFET Configuration

MOSFET Selection

The MAX4838–MAX4841 are designed for use with either a single N-channel MOSFET or dual back-to-back N-channel MOSFETs. In most situations, MOSFETs with RDS(ON) specified for a VGS of 4.5V work well. If the input supply is near the UVLO maximum of 3.5V consider using a MOSFET specified for a lower VGS voltage. Also the VDS should be 30V for the MOSFET to withstand the full 28V IN range of the MAX4838–MAX4841. Table 1 shows a selection of MOSFETs appropriate for use with the MAX4838–MAX4841.

IN Bypass Considerations

For most applications, bypass IN to GND with a $1\mu F$ ceramic capacitor. If the power source has significant inductance due to long lead length, take care to prevent overshoots due to the LC tank circuit and provide protection if necessary to prevent exceeding the 30V absolute maximum rating on IN.

The MAX4838–MAX4841 provide protection against voltage faults up to 28V, but this does not include negative voltages. If negative voltages are a concern, connect a Schottky diode from IN to GND to clamp negative input voltages.

ESD Test Conditions

ESD performance depends on a number of conditions. The MAX4838–MAX4841 are specified for 15kV typical ESD resistance on IN when IN is bypassed to ground with a 1 μ F ceramic capacitor. Contact Maxim for a reliability report that documents test setup, methodology, and results.



Table 1. MOSFET Suggestions

PART	CONFIGURATION/ PACKAGE	V _{DS} MAX (V)	R _{ON} AT 4.5V (mΩ)	MANUFACTURER	
Si9936DY	Dual/SO8	30	80	Vishay Siliconix	
Si5904DC	Dual/1206-8	30	143	www.vishay.com	
Si1426DH	Single/SC70-6	30	115	402-563-6866	
FDC6305N	Dual/SSOT-6	20	80	Fairchild Semiconductor	
FDS8926A	Dual/SO8	30	20	www.fairchildsemi.com	
FDG315N	Single/SC70-6	30	160	207-775-8100	
IRF7752	Dual/TSSOP-8	30	36	International Rectifier	
IRF7303	Dual/SO8	30	80	www.irf.com	
IRF7607	Single/Micro-8	20	30	310-322-3331	

Human Body Model

Figure 8 shows the Human Body Model and Figure 9 shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the device through a $1.5 \mathrm{k}\Omega$ resistor.

IEC 1000-4-2

Since January 1996, all equipment manufactured and/or sold in the European community has been required to meet the stringent IEC 1000-4-2 specification. The IEC 1000-4-2 standard covers ESD testing and performance of finished equipment; it does not specifically refer to integrated circuits. The MAX4838–MAX4841 help users

design equipment that meets Level 3 of IEC 1000-4-2, without additional ESD-protection components.

The main difference between tests done using the Human Body Model and IEC 1000-4-2 is higher peak current in IEC 1000-4-2. Because series resistance is lower in the IEC 1000-4-2 ESD test model (Figure 10), the ESD-withstand voltage measured to this standard is generally lower than that measured using the Human Body Model. Figure 11 shows the current waveform for the ±8kV IEC 1000-4-2 Level 4 ESD Contact Discharge test. The Air-Gap test involves approaching the device with a charger probe. The Contact Discharge method connects the probe to the device before the probe is energized.

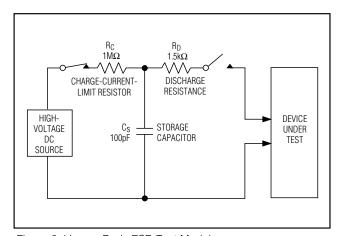


Figure 8. Human Body ESD Test Model

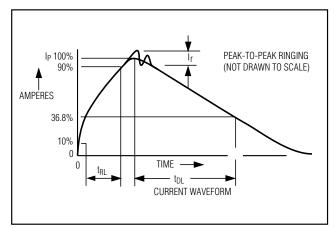


Figure 9. Human Body Model Current Waveform

MIXNN

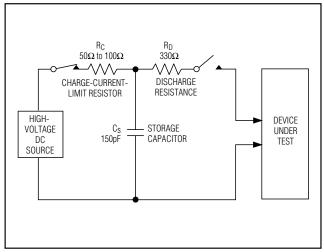


Figure 10. IEC 1000-4-2 ESD Test Model

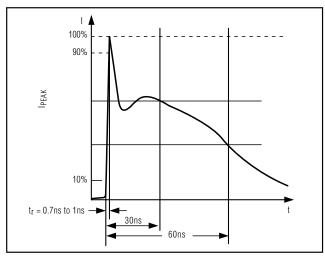


Figure 11. IEC 1000-4-2 ESD Generator Current

Pin Configuration

TOP VIEW

IN 1
GND 2
MAXIM
MAX4838MAX4841

5 N.C.

FLAG 3
4 GATE

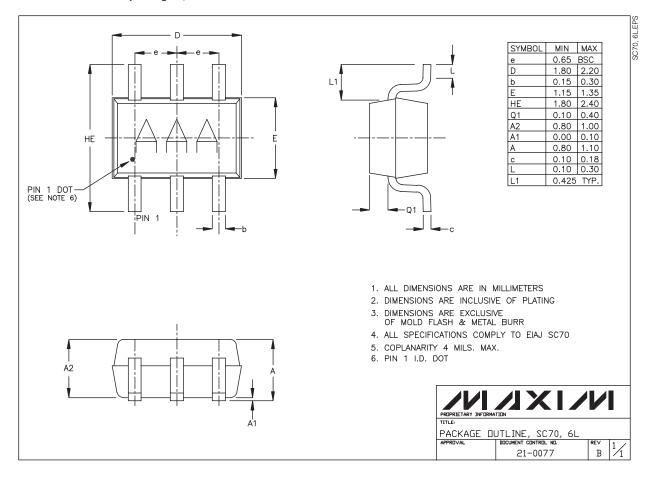
() FOR MAX4839 AND MAX4841 ONLY.

Chip Information

TRANSISTOR COUNT: 737 PROCESS: BICMOS

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-ic.com/packages.)



Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

10 _____Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086 408-737-7600

© 2003 Maxim Integrated Products

Printed USA

is a registered trademark of Maxim Integrated Products.